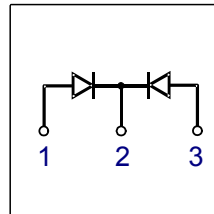
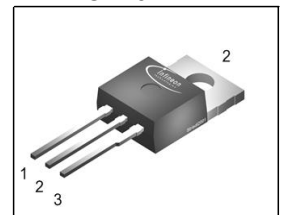


Silicon Carbide Schottky Diode

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

thinQ!TM SiC Schottky Diode

Product Summary

V_{RRM}	300	V
Q_C	23	nC
I_F	2x10	A

P-TO220


Type	Package	Ordering Code	Marking
SDP20S30	P-TO220-3	Q67040-S4419	D20S30

Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified (per leg)

Parameter	Symbol	Value	Unit
Continuous forward current, $T_C=100^\circ\text{C}$	I_F	10	A
RMS forward current, $f=50\text{Hz}$	I_{FRMS}	14	
Surge non repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	I_{FSM}	36	
Repetitive peak forward current $T_j=150^\circ\text{C}$, $T_C=100^\circ\text{C}$, $D=0.1$	I_{FRM}	45	
Non repetitive peak forward current $t_p=10\mu\text{s}$, $T_C=25^\circ\text{C}$	I_{FMAX}	100	
i^2t value, $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$	$\int i^2 dt$	6.5	A ² s
Repetitive peak reverse voltage	V_{RRM}	300	V
Surge peak reverse voltage	V_{RSM}	300	
Power dissipation, single diode mode, $T_C=25^\circ\text{C}$	P_{tot}	65	W
Operating and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case (per leg)	R_{thJC}	-	-	2.3	K/W

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified (per leg)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Diode forward voltage	V_F				V
$I_F=10\text{A}, T_j=25\text{ }^\circ\text{C}$		-	1.5	1.7	
$I_F=10\text{A}, T_j=150\text{ }^\circ\text{C}$		-	1.5	1.9	
Reverse current	I_R				μA
$V_R=300\text{V}, T_j=25\text{ }^\circ\text{C}$		-	15	200	
$V_R=300\text{V}, T_j=150\text{ }^\circ\text{C}$		-	20	1000	

⁰J-STD20 and JESD22

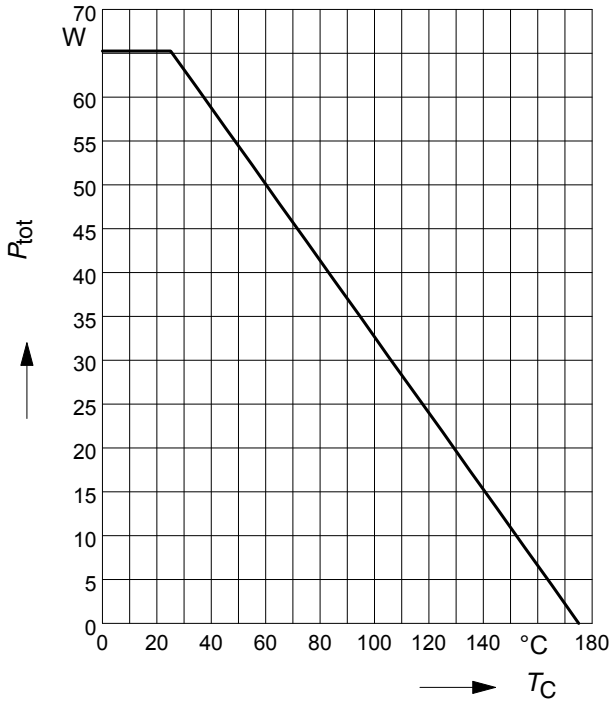
¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified (per leg)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Total capacitive charge ¹⁾ $V_R=200\text{V}$, $I_F=10\text{A}$, $di_F/dt=-200\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	Q_C	-	23	-	nC
Switching time ²⁾ $V_R=200\text{V}$, $I_F=10\text{A}$, $di_F/dt=-200\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	t_{rr}	-	n.a.	-	ns
Total capacitance $V_R=0\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$ $V_R=150\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$ $V_R=300\text{V}$, $T_C=25\text{°C}$, $f=1\text{MHz}$	C	-	600 55 40	-	pF

1 Power dissipation (per leg)

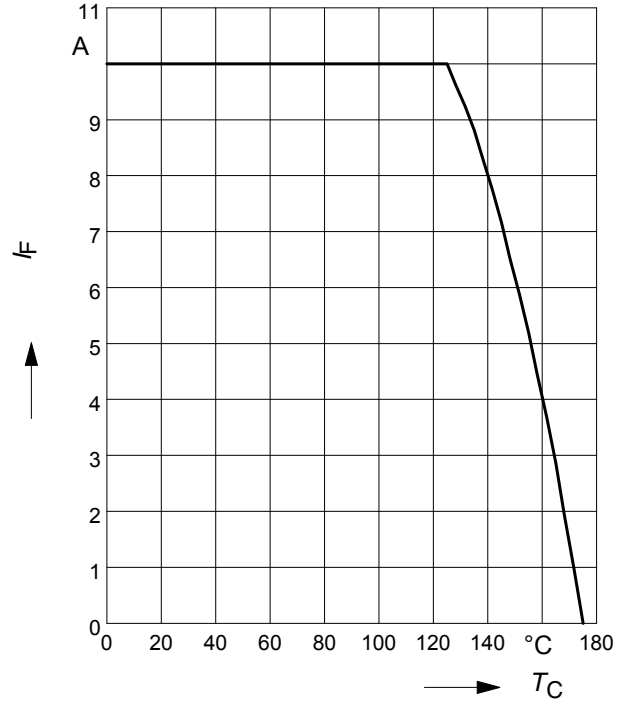
$P_{tot} = f(T_C)$



2 Diode forward current (per leg)

$I_F = f(T_C)$

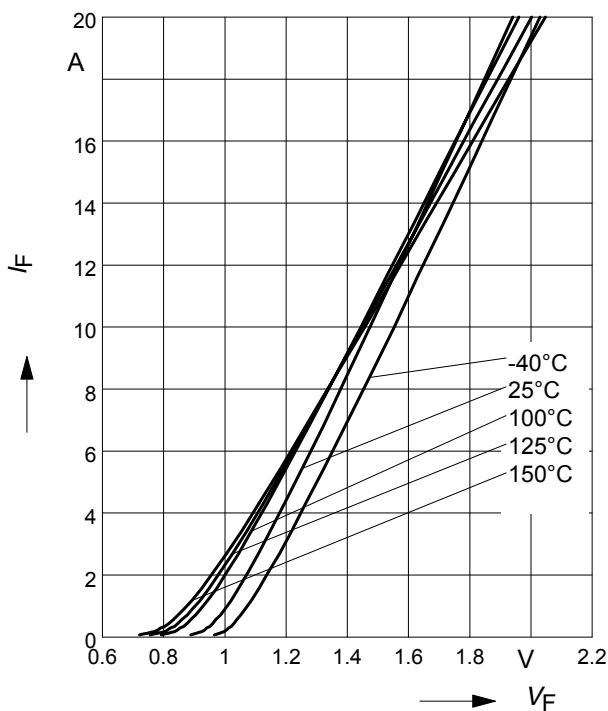
parameter: $T_j \leq 175^\circ\text{C}$



3 Typ. forward characteristic (per leg)

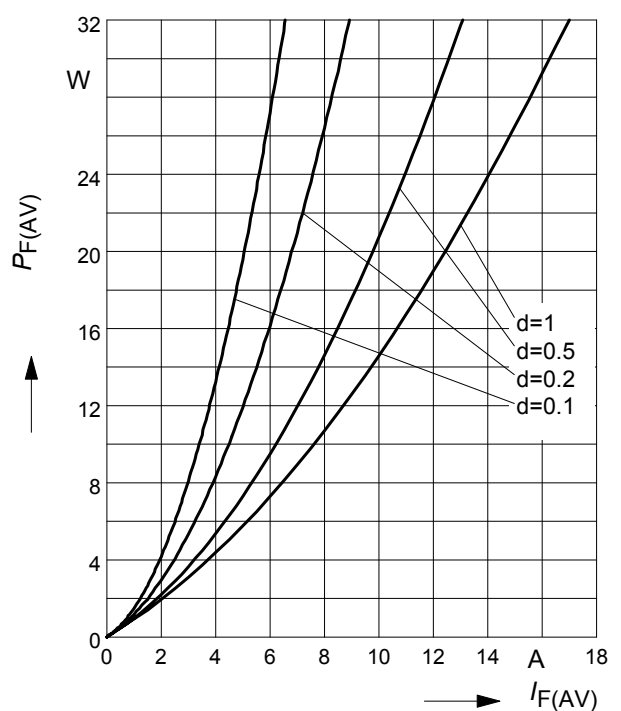
$I_F = f(V_F)$

parameter: $T_j, t_p = 350 \mu\text{s}$

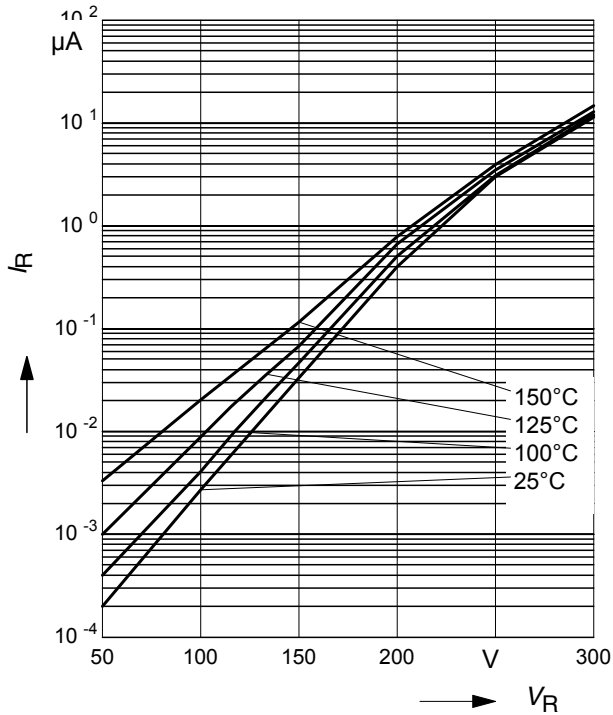


4 Typ. forward power dissipation vs. average forward current (per leg)

$P_{F(AV)} = f(I_F) \quad T_C = 100^\circ\text{C}, d = t_p/T$



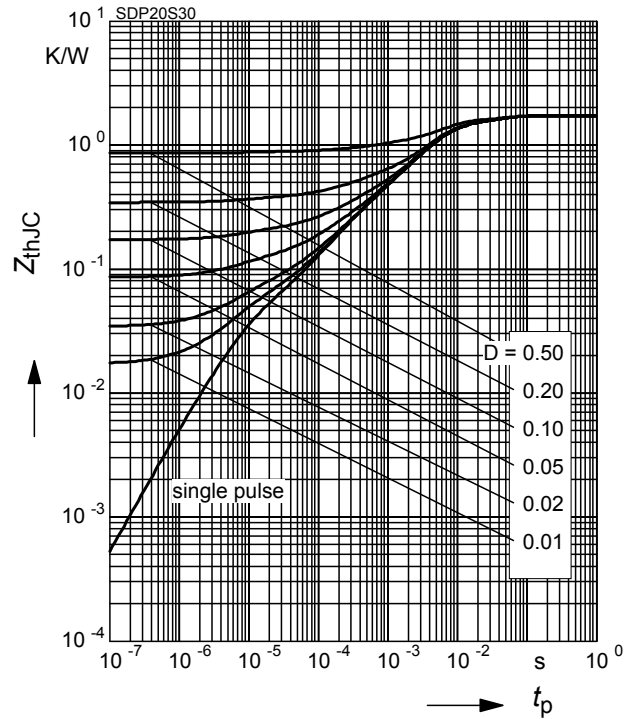
5 Typ. reverse current vs. reverse voltage
(per leg) $I_R = f(V_R)$



6 Transient thermal impedance (per leg)

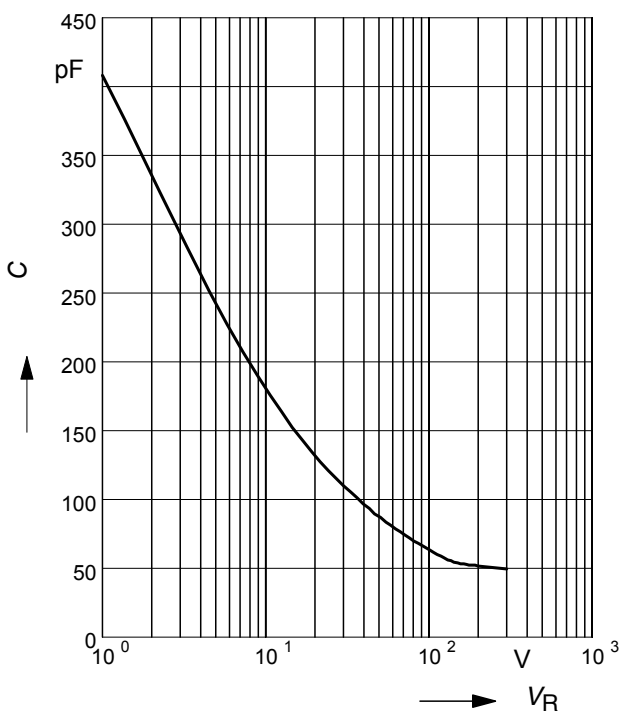
$Z_{thJC} = f(t_p)$

parameter : $D = t_p/T$



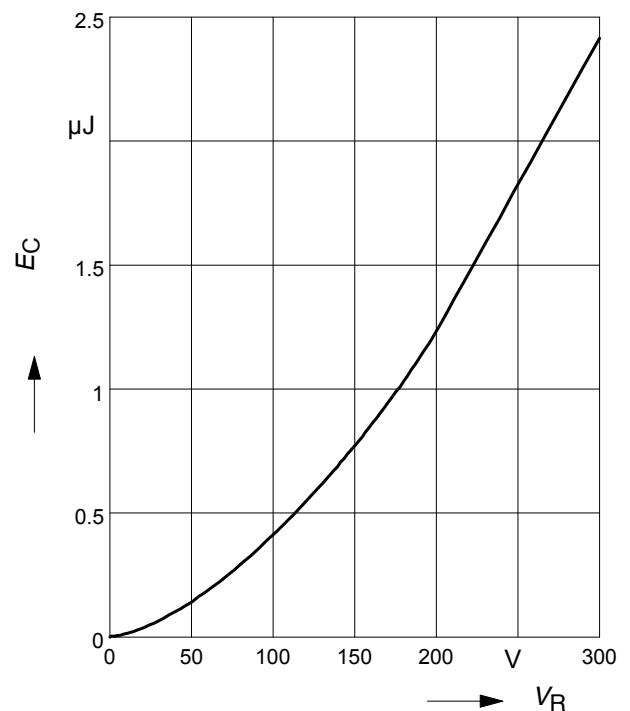
7 Typ. capacitance vs. reverse voltage
(per leg) $C = f(V_R)$

parameter: $T_C = 25^\circ C, f = 1 MHz$



8 Typ. C stored energy (per leg)

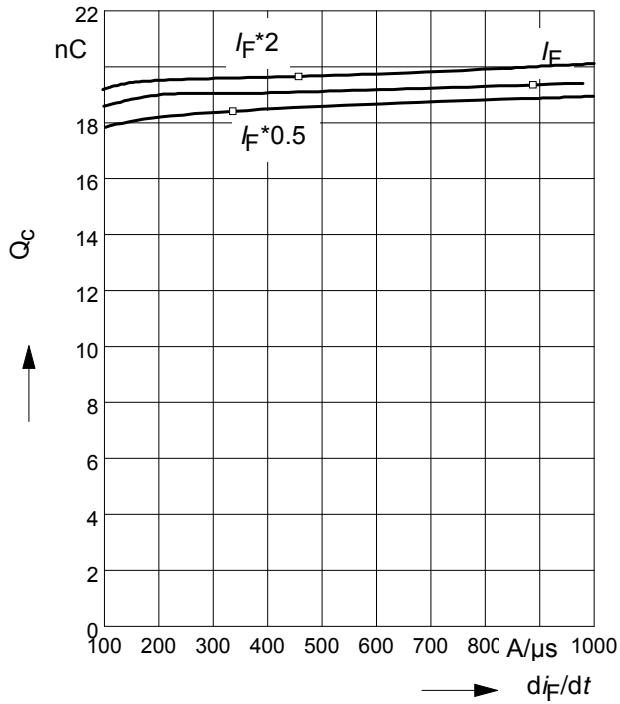
$E_C = f(V_R)$



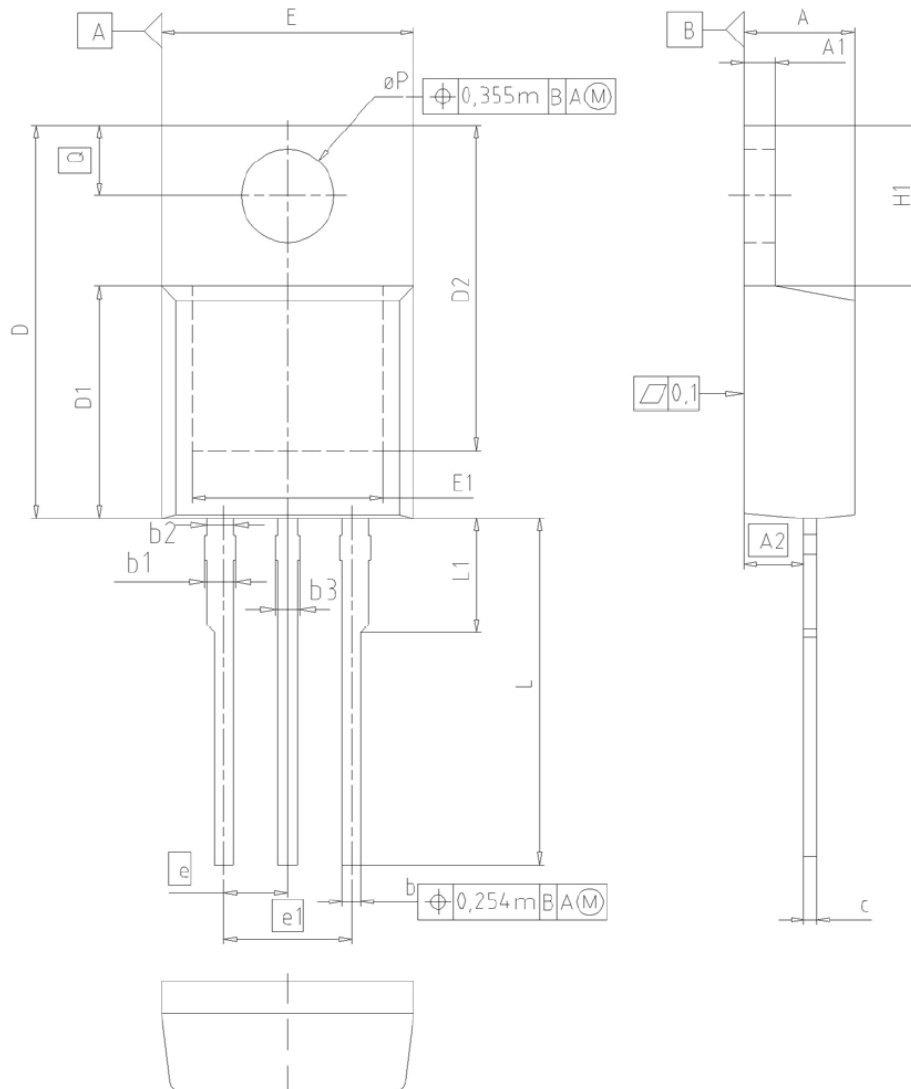
9 Typ. capacitive charge vs. current slope

(per leg) $Q_c = f(di_F/dt)$

parameter: $T_j = 150\text{ }^\circ\text{C}$



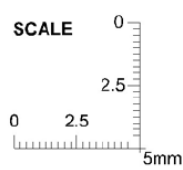
P-TO220-3-1, P-TO220-3-21




DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
ϕP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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SCALE



EUROPEAN PROJECTION



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